Under the Bas Work Reduction Act of 1995 TRANSMITTAL FORM (to be used for all correspondence after initial) Total Number of Pages in This Submission	Art Unit Examiner Name Application Number Filing Date First Named Inventor Art Unit Examiner Name	Approved for use through 07/31/2006. OMB 0651-0031 atent and Trademark Office; U.S. DEPARTMENT OF COMMERCE ection of information unless it displays a valid OMB control number. 10/655,904 Sept. 5, 2003 James D. Parsons 2878 Otilia Gabor 378-21-034
Fee Transmittal Form Fee Attached Amendment/Reply After Final Affidavits/declaration(s) Extension of Time Request Express Abandonment Request Information Disclosure Statement Certified Copy of Priority Document(s) Reply to Missing Parts/ Incomplete Application Reply to Missing Parts under 37 CFR 1.52 or 1.53	Drawing(s) Licensing-related Papers Petition Petition to Convert to a Provisional Application Power of Attorney, Revocation Change of Correspondence A Terminal Disclaimer Request for Refund CD, Number of CD(s) Landscape Table on CD Remarks	After Allowance Communication to TC Appeal Communication to Board of Appeals and Interferences Appeal Communication to TC (Appeal Notice, Brief, Reply Brief) Proprietary Information Status Letter Other Enclosure(s) (please Identify below): Itemized Postcard Substitute Appeal Brief (18 pages) Request for Waiver of Additional Appeal Fees (2 pages)
Firm Name KOPPEL, JACOBS, PATE	TURE OF APPLICANT, ATTO	RNEY, OR AGENT
Printed name RICHARD S. KOPPEL Date 1/9/06	fdggel	Reg. No. 26,475

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Check Credit Card Money Order None Other (please identify): Deposit Account Deposit Account Number: 11-1580 Deposit Account Name: Richard S. Koppel For the above-identified deposit account, the Director is hereby authorized to: (check all that apply) Charge fee(s) indicated below Charge fee(s) indicated below Charge any additional fee(s) or underpayments of fee(s) Credit any overpayments WARNING: Information on this form may become public. Credit card Information should not be included on this form. Provide credit card Information and authorization on PTO-2038.							
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Name (Print/Type)	Richard S. Koppel	77		Date //9/06

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AP

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Appl. No. : 10/655,904

Applicant : JAMES D. PARSONS

Filed : Sept. 5, 2003

TC/A.U. : 2878

JAN O 9 2006

Examiner : OTILIA GABOR

Docket No. : 378-21-034

Customer No. : 23935

Title: ACOUSTIC ABSORPTION RADIATION SENSING IN SiC

Mail Stop Appeal Brief - Patents Commissioner for Patents P.O. Box 1450 Alexandria VA 22313-1450

REQUEST FOR WAIVER OF ADDITIONAL APPEAL FEES

Applicant appealed from the Final Office Action dated August 5, 2005 and paid the applicable fees for both the Notice of Appeal and the Appeal Brief. aminer thereafter reopened prosecution in response to the Appeal Brief with a new Final Office Action dated December 1, 2005, and applicant now appeals from the new Final The new Final Action corrected for an error in Action. the original Final Action that was noted in appellant's original Appeal Brief, and also for an omission in stating a reason for the rejection of certain dependent claims in the original Final Action. Since the need for filing a new Notice of Appeal and Appeal Brief arose through errors on the part of the Office, and the original appeal has not yet been considered by the Board, it is requested that the fees paid in connection with the original appeal be applied to the present notice of apAppl. No. 10/655,904 January 9, 2006 Page 2 of 2

peal and appeal brief in connection with the new Final Action. However, if this request is not granted, the Office is authorized to charge the small entity Notice of Appeal and Appeal Brief fee to Deposit Account No. 11-1580. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

Dated: (/9/06

Richard S. Koppel

Registration No. 26,475 Attorney for Appellant

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Appl. No. : 10/655,904

Applicant : JAMES D. PARSONS

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SUBSTITUTE APPEAL BRIEF

TABLE OF CONTENTS

	Page
Real Party in Interest	1
Related Appeals and Interferences	
Status of Claims	3
Status of Amendments	4
Summary of Claimed Subject Matter	5
Grounds of Rejection to be Reviewed on Appeal	6
Argument	7
Claims Appendix	13
Evidence Appendix	16
Related Proceedings Appendix	17

(1) Real Party in Interest

The real party in interest is Heetronix, a Nevada corporation and assignee of record of the above application.

(2) Related Appeals and Interferences

Appellant previously appealed from the Final Office action dated August 5, 2005, and filed an Appeal Brief on November 4, 2005 noting that the identification of claims 6 and 22-26 as being rejected on the cover sheet of the August 5, 2005 Final Action appeared to be an error. Appeal Brief argued that claim 6 should have been identified as being allowable if rewritten in independent form, and that claims 22-26 should have been allowed outright. In response, the Examiner issued a new Final Action on December 1, 2005 allowing claims 22-26, and objecting to claim 6 as being dependent upon a rejected base claim, but being allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims. The new Final Action also added a recitation of grounds for the rejection of claims 7, 8 and 18 that had not been included in the original Final Action, and in addition identified for the first time a feature that is not specifically disclosed in the Ichikawa reference.

Appellant considers the December 1, 2005 Final Action to have replaced the original August 5, 2005 Final Action, and therefore considers this Appeal Brief as a substitute for the original Appeal Brief filed November 4, 2005.

(3) Status of Claims

Claims 1-5 and 7-21: rejected and appealed.

Claims 22-26: allowed.

Claim 6: objected to but found allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.

(4) Status of Amendments

An amendment rewriting claim 6 in independent form is being filed concurrently with this Substitute Appeal Brief. No other amendments have been filed subsequent to final rejection.

(5) Summary of Claimed Subject Matter

The invention enables the use of SiC to detect electromagnetic radiation (ER) at wavelengths less than about 10 micrometers. (Specification page 3, lines 2-8; page 3, line 34 - page 4, line 1). This is accomplished through the use of an acoustic absorption mechanism in SiC (page 3, lines 6-12; page 4, lines 7-26; page 6, lines 30-35; page 7, lines 2-7; Fig. 1, SiC body 6). To achieve acoustic absorption in SiC, the thickness of the SiC body is preferably at least about 400 micrometers (page 3, lines 7-12; page 4, lines 19-26; Fig. 1, SiC body 6). The SiC body preferably has a uniform thickness (page 3, lines 16-9; page 6, lines 30-32; Fig. 1, SiC body 6).

Independent claim 1 requires a SiC body at least about 400 micrometers thick, and a detector arranged to detect acoustic absorption of ER having a wavelength less than about 10 micrometers by the SiC body.

Dependent claims 7 and 8, argued separately, include the requirements of claim 1 and in addition require that the thickness of the SiC body be uniform (claim 7), and that the body have a flat radiation receiving surface (claim 8).

Independent claim 9 claims the method of deleting ER by irradiating a SiC body at least about 400 micrometers thick with ER having a wavelength less than about 10 micrometers, and detecting an acoustic absorption response of the SiC body to the radiation

Independent claim 14 claims the method of deleting ER by irradiating a SiC body at least about 400 micrometers thick with ER having a wavelength less than about 10 micrometers, and detecting a response of the SiC body to the radiation.

Independent claim 19 claims the method of detecting ER by irradiating a uniform thickness body of SiC with radiation having a wavelength less than about 10 micrometers, and detecting acoustic absorption of the radiation by the body.

(6) Grounds of Rejection to be Reviewed on Appeal

(a) Whether claims 1-5 and 7-21 are unpatentable under 35 U.S.C.103(a) over Ichikawa.

(7) Argument

(a) Rejection Under 35U.S.C.103(a) over Ichikawa

(i) Claims 1-5 and 9-13

A Claimed Range That Overlaps a Prior Art Range Can Be Patentable

Each of these claims require the detection of ER having a wavelength less than about 10 micrometers by an SiC body having a thickness of at least about 400 micrometers, by detecting acoustic absorption of the ER.

These claims were rejected under 35U.S.C.103(a) over Ichikawa (U.S. Patent No. 5,025,243). This rejection was based in part upon these claims involving a detection of radiation having a wavelength less than about 10 micrometers, Ichikawa disclosing a detection of infrared radiation, and an assertion that the "near" and "intermediate" infrared ranges are covered by the recited "less than about 10 micrometers" range.

However, Ichikawa does not disclose any particular portion of the infrared spectrum at which it operates; it merely refers throughout its disclosure to infrared radiation in general. As recently confirmed by the Federal Circuit in In re Kumer, 418 F.3d 1361, 1366 (Fed. Cir. 2005), "A prima facie case of obviousness may be made when the only difference from the prior art is a difference in the range or value of a particular variable. [cites omitted]" The Court went on to recite examples of how such a prima facie case could be rebutted:

"An applicant may rebut a prima facie case of obviousness by providing a "showing of facts supporting the opposite conclusion." Such a showing dissipates the prima facie holding and requires the examiner to "consider all of the evidence anew." Piasecki, 745 F.2d at 1472; In re Rinehart, 531 F.2d 1048, 1052 (CCPA 1976). Rebuttal evidence may show, for example, that the claimed invention achieved unexpected results relative to the prior art, <u>In re Geisler, 116 F.3d 1465, 1469-70 (Fed.</u> Cir. 1997); that the prior art teaches away from the claimed invention, id. at 1471; that objective evidence (e.g., commercial success) supports the conclusion that the invention would not have been obvious to a skilled artisan, Piasecki, 745 F.2d at 1475; or that the prior art did not enable one skilled in the art to produce the now-claimed invention, In re Payne, 606 F.2d 303, 314-15 (CCPA 1979)." (418 F.3d at 1368).

Infrared radiation is defined as the region of the electromagnetic spectrum between 0.7 and 1,000 micrometers. (see Van Nostrand's Scientific Encyclopedia, seventh edition, Van Nostrand Reinhold, 1989, page 1551, cited in the May 25, 2005 Amendment). Thus, the portion of the infrared spectrum "having a wavelength less than about 10 micrometers", as claimed, represents approximately one percent of the overall infrared range.

Finding a way to operate in the narrow portion of the infrared range below 10 micrometers constituted an "unexpected result" because, as stated at page 1, line 26 - page 2, line 3 of the specification, "acoustic absorption has not been observed in SiC for wavelengths below about 10 micrometers, thus eliminating part of the IR band along with shorter wavelengths". The other radiation absorption mechanisms either do not function in the infrared range (bandgap absorption, page 21, lines 4-18), or occur only at the specific wavelengths corresponding to the absorption energy of an impurity in the SiC (page 2, lines 19-34). Acoustic absorption "is a desirable absorption mechanism when the detection is sought over a broad range of wavelengths, since it causes the resistance of a SiC chip to increase approximately linearly with the irradiating energy over an appreciable wavelength range" (page 1, lines 15-21).

Since it was not known in the art that SiC would absorb infrared radiation below 10 micrometers by acoustic absorption, and in fact no such absorption had previously been observed (page 1, line 24 - page 2, line 3), appellant has overcome the prima facie case of obviousness by showing that SiC actually can be made to exhibit substantial acoustic absorption for infrared wavelengths less than 10 micrometers. This discovery constituted an unexpected result that was contrary to the knowledge in the art at the time the invention was made.

While it was known that, for a correctly selected impurity, SiC would exhibit absorption for infrared wavelengths less than 10 micrometers, such absorption occurred only at specific wavelengths corresponding to the impurity absorption energy, not at other wavelengths. This was an impurity absorption mechanism, not acoustic absorption. The distinction between acoustic and impurity absorption is further emphasized in the application as follows: "IR radiation absorbed via acoustic absorption is converted directly into heat energy and causes the resistance of the SiC to increase roughly linearly with the IR energy, as opposed to impurity absorption

which causes the SiC resistance to drop." (Page 4, lines 14-18). Appellant's discovery of a broad band acoustic absorption mechanism in SiC, as opposed to very narrow band impurity absorption, at infrared wavelengths below 10 micrometers, offers distinct advantages over the previously known impurity absorption mechanism.

There is no suggestion in Ichikawa of detecting the approximately 1% of the IR range having a wavelength less than about 10 micrometers, or of employing an acoustic absorption mechanism within this wavelength range. In fact, Ichikawa suggests that, even if the incident IR were selected to be less than 10 micrometers, any resulting absorption would not have been the result of acoustic absorption. Ichikawa however, discloses a SiC monofilament or fibers with a diameter in the 3 - 200 micrometer range. The diameter of the irradiated filament ranged from 8 to 30 microns in the actual examples given. This contrasts with the preferred embodiment of the present invention:

"Whereas no acoustic absorption has been observed for SiC at wavelengths below about 10 micrometers, applicant has discovered that a useful acoustic absorption mechanism can be obtained from SiC if it has a single crystal structure and its thickness is at least about 200 micrometers. While there may be some acoustic absorption with thinner samples, the amount is so small that it has not previously been observed." (Specification page 4, lines 7-14).

The SiC dimensions used in Ichikawa were too small to result in any observable acoustic absorption at wavelengths below 10 micrometers. Even at Ichikawa's upper limit of a 200 micron diameter (considerably larger than any of the fibers used in his examples), the fiber would be 200 microns thick only along its (infinitely narrow) center axis, which would not be enough for any appreciable acoustic absorption. The rejected claims, except for 19-21, all require that the thickness of the SiC body be at least about 400 micrometers, the preferred thickness given in the specification (page 3, lines 7-12; page 4, lines 23-26). In disclosing a fiber that is everywhere thinner than 200 microns except for an infinitely thin center diameter, and thus no more than half of applicant's claimed thickness, Ichikawa actually teaches away from applicant's concept of achieving acoustic absorption for wavelengths less than about 10 micrometers by providing a SiC body that is at least about 400 micrometers thick. Even with a 200 micron diameter, Ichikawa would not achieve any appreciable IR acoustic absorption at less than 10 micrometers.

- All of the above arguments were presented in the Amendment immediately preceding the Final Rejection. Although the Final Rejection included a section labeled "Response to Arguments," it simply ignored and did not respond to the following augments made by appellant:
- 1) The claimed wavelength range of less than about 10 micrometers within the 0.7 1,000 micrometer infrared band is critical, achieving the unexpected result of acoustic absorption for this range in which acoustic absorption had not previously been observed.
- 2) Ichikawa taught a fiber diameter of up to a maximum of 200 micrometers, only along an infinitely thin diameter, which would not have produced observable acoustic absorption.
- 3) Increasing Ichikawa's maximum dimension of 200 micrometers up to the minimum claimed thickness of about 400 micrometers would not have been obvious because the purpose of such an increase would have been to enhance acoustic absorption, whereas acoustic absorption had not previously been observed in SiC below 10 micrometers wavelength.
- 4) Using a greater SiC thickness does not merely change the size of the acoustic absorption, as claimed by the Examiner. No acoustic absorption at all is observable for thicknesses less than about 200 micrometers within the claimed wavelength range.

(ii) Claims 7, 8

These claims, which depend from claim 1, require that the thickness of the SiC body be uniform (claim 7), and that the body have a flat radiation receiving surface The Examiner argued that "... since Ichikawa (claim 8). does not disclose that the thickness of the body F changes throughout or that its surface roughness changes, it is assumed that the body F has uniform thickness and a The Examiner further stated that "Ichiflat surface." kawa does not disclose any protrusions and/or surface irregularities in the SiC body and therefore, it is considered to be flat (no protrusions) and having a uniform thickness (uniform thickness and flatness of surface is present even if the filament is cylindrical). ally, body F of Ichikawa is shown as having a circular cross-section in FIGs. 1(b), 2(a) and 2(b), and is referred to as having a "monofilament diameter" at column 1, lines 63-64. There is no disclosure or suggestion of a SiC body with a uniform thickness or flat surface.

The Examiner's equating of the term "flat" with a lack of "protrusions and/or surface irregularities" contradicts the commonly accepted definitions of "flat", nor is any support for the Examiner's interpretation of "flat" provided by applicant's specification. The following relevant definitions of "flat" are given in Random House Webster's College Dictionary, Random House New York, 1998, page 494: "1. horizontally level. 2. level, even, or without unevenness of surface, as land or tabletops. 3. having a surface that is without marks, projects or depressions. 4. lying horizontally and at full length... 9. spread out, as an unrolled map or the open hand... 28. a flat surface, side, or part of anything... 34. an iron or steel bar of rectangular cross-section."

The body F of Ichikawa which the Examiner refers to is shown as having a circular cross-section in FIGs. 1(b), 2(a) and 2(b), and is referred to as having a "monofilament diameter" at column 1, lines 63-64. The proposition that a circular cross-section is "flat" goes against the normal meaning of the word. A diameter of the circular cross-section of Ichikawa's body would be "flat", but the semi-circle on either side of that diameter would be a "projection" that contradicts flatness. Ichikawa accordingly does not have a "flat" surface.

The position that a body with a circular crosssection has a "uniform thickness" also contradicts the commonly accepted meaning of "uniform". The applicable definitions of "uniform" on page 1404 of the same dictionary are "1. identical or consistent... without variations in detail: a uniform surface. 3. constant; unvarying..." By definition, a circular body does not have a "uniform" thickness. A section taken through the center of the body has maximum thickness; that thickness becomes progressively smaller as the section is moved to This contrasts directly with the body 6 either side. shown in applicant's preferred embodiment of Fig. 1, in which the two principal surfaces are indeed flat and parallel to each other, with an equidistant spacing between them at all points.

(iii) Claims 14-18

These claims require an irradiating wavelength of less than about 10 micrometers and a SiC body at lest

about 400 micrometers thick, but do not require acoustic absorption. However, the achievement of acoustic absorption for wavelengths below about 10 micrometers was appellant's motivation for this thickness. Since, as explained above, acoustic absorption has not been observed within this wavelength range with either Ichikawa or other prior art known to appellant, there would have been no motivation to increase the Ichikawa thickness to 400 micrometers.

(iv) Claims 19-21

These claims require irradiating a uniform thickness SiC body of SiC at a wavelength less than about 10 micrometers, and detecting acoustic absorption of the radiation by the body. Neither Ichikawa nor any other prior art known to appellant either discloses, suggests or operates by acoustic absorption in SiC at wavelengths below about 10 micrometers. Furthermore, the Examiner erroneously stated in the Final Rejection that "Ichikawa does not disclose the thickness of the body F changes throughout or that its surface roughness changes", and concluded that "it is assumed that the body F has uniform thickness and a flat surface". Actually, body F of Ichikawa is shown as having a circular cross-section in FIGs. 1(b), 2(a) and 2(b), and is referred to as having a "monofilament diameter" at column 1, lines 63-64. was pointed out to the examiner in the Amendment preceding the Final Office action, but was ignored in that action. Ichikawa's circular cross-section negates the uniform thinness and flat surface claimed for it by the Examiner.

Respectfully submitted,

Pated: 1/9/6

Richard S. Koppel

Registration No. 26,475 Attorney for Appellant

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CLAIMS APPENDIX

5

- 1. An electromagnetic radiation detection system, comprising:
- a body of SiC having a thickness of at least about 400 micrometers, and
- a detector arranged to detect acoustic absorption of electromagnetic radiation having a wavelength less than about 10 micrometers by said SiC body.
- 2. The system of claim 1, wherein said detector is arranged to detect infrared (IR) radiation absorption by said SiC body.
- 3. The system of claim 1, wherein the thickness of said SiC body is in the approximate range of 400-2,000 micrometers.
- 4. The system of claim 1, wherein said detector is arranged to detect increases in the resistance of said SiC body in response to said body receiving radiation having a wavelength less than about 10 micrometers.
- 5. The system of claim 1, further comprising a filter arranged to limit the reception of radiation by said SiC body to a narrow wavelength band.
- 7. The system of claim 1, wherein the thickness of said SiC body is uniform.
- 8. The system of claim 1, wherein said SiC body has a radiation receiving surface that is flat.

9. An electromagnetic radiation detection method, comprising:

irradiating a body of SiC having a thickness of at least about 400 micrometers with electromagnetic radiation having a wavelength less than about 10 micrometers, and

detecting an acoustic absorption response of said SiC body to said radiation.

- 10. The method of claim 9, wherein said SiC body is irradiated with infrared (IR) radiation.
- 11. The method of claim 9, wherein the thickness of said SiC body is in the approximate range of 400-2,000 micrometers.
- 12. The method of claim 9, wherein said acoustic absorption is detected by detecting increases in the resistance of said SiC body in response to said radiation.
- 13. The method of claim 9, wherein said radiation comprises a band of multiple wavelengths.
- 14. An electromagnetic radiation detection method, comprising:

irradiating a body of SiC having a thickness of at least about 400 micrometers with electromagnetic radiation having a wavelength less than about 10 micrometers, and

detecting a response of said SiC body to said radiation.

15. The method of claim 14, wherein said SiC body is irradiated with infrared (IR) radiation.

- 16. The method of claim 14, wherein the thickness of said SiC body is in the approximate range of 400-2,000 micrometers.
- 17. The method of claim 14, wherein said response is detected by detecting increases in the resistance of said SiC body in response to said radiation.
- 18. The method of claim 14, wherein said SiC body has a uniform thickness.
- 19. An electromagnetic radiation detection method, comprising:

irradiating a uniform thickness body of SiC with radiation having a wavelength less than about 10 micrometers, and

detecting acoustic absorption of said radiation by said body.

- 20. The method of claim 19, wherein said SiC body is irradiated with infrared (IR) radiation.
- 21. The method of claim 19, wherein said acoustic absorption is detected by detecting increases in the resistance of said SiC body in response to said radiation.

EVIDENCE APPENDIX

None

RELATED PROCEEDINGS APPENDIX

None